

Thermal resistance

Parameter	Symbol	Min.	Typ.	Max.	Unit
Thermal resistance, junction - case	R_{thJC}	-	-	1.5	$^{\circ}C/W$
Thermal resistance, junction - ambient	R_{thJA}	-	-	37	$^{\circ}C/W$
Soldering temperature, wave soldering for 10s	T_{sold}	-	-	265	$^{\circ}C$

Parameter	Symbol	Condition	Min.	Typ	Max.	Unit
Drain-Source Breakdown Voltage	BV_{DSS}	$V_{GS}=0V, I_D=-250\mu A$	-30			V
Gate Threshold Voltage	$V_{GS(TH)}$	$V_{GS}=V_{DS}, I_D=-250\mu A$	-1.2		-2.5	V
Drain-Source Leakage Current	I_{DSS}	$V_{DS}=-30V, V_{GS}=0V$			1.0	μA
Gate- Source Leakage Current	I_{GSS}	$V_{GS}=\pm 20V, V_{DS}=0V$			100	nA
Static Drain-source On Resistance		$V_{GS}=-10V, I_D=-24A$				
		$V_{GS}=-4.5V, I_D=-12A$				
Forward Transconductance	g_{FS}	$V_{DS}=-25V, I_D=-10A$				
Source-drain voltage	V_{SD}	$I_S=-24A$				

Parameter	Symbol	Condition	Min.	Typ	Max.	Unit
Input capacitance	C_{iss}	$V_{GS}=0V, V_{DS}=20V$ $f = 1MHz$	-	4500	-	pF
Output capacitance	C_{oss}		-	398	-	
Reverse transfer capacitance	C_{rss}		-	157	-	

Gate Charge characteristics($T_a = 25$)

Parameter	Symbol	Condition	Min.	Typ	Max.	Unit
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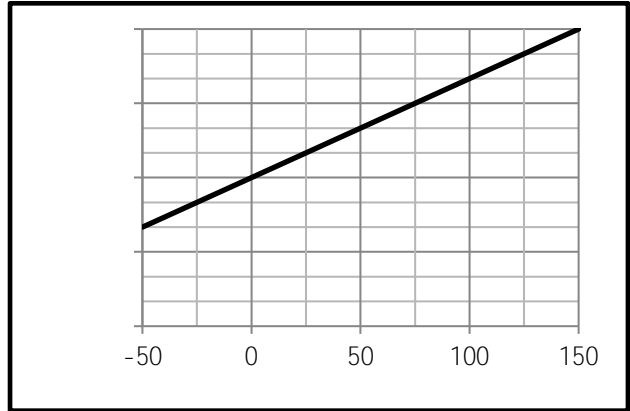
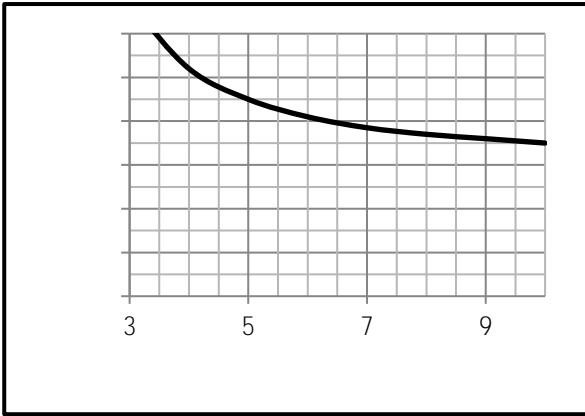


Fig.10 I_D -Junction Temperature

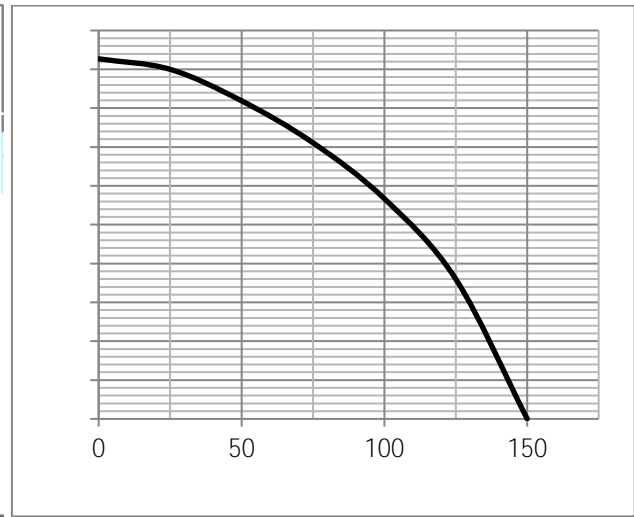
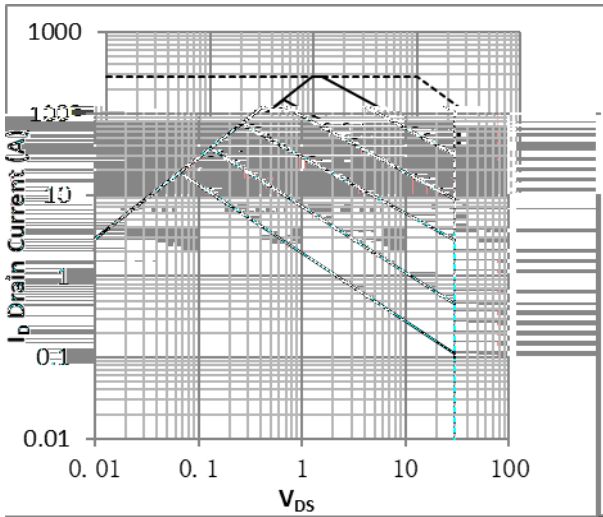


Fig.9 Switching Time Measurement Circuit

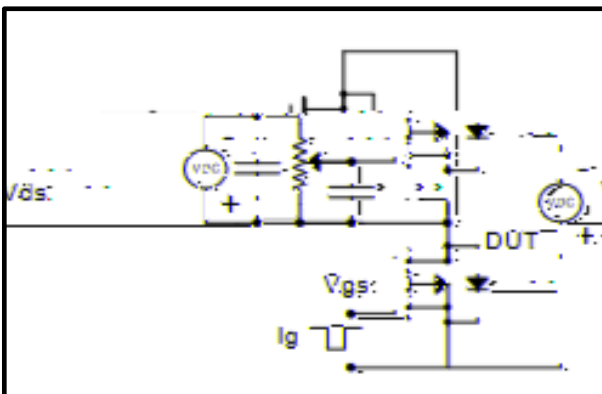


Fig.10 Gate Charge Waveform

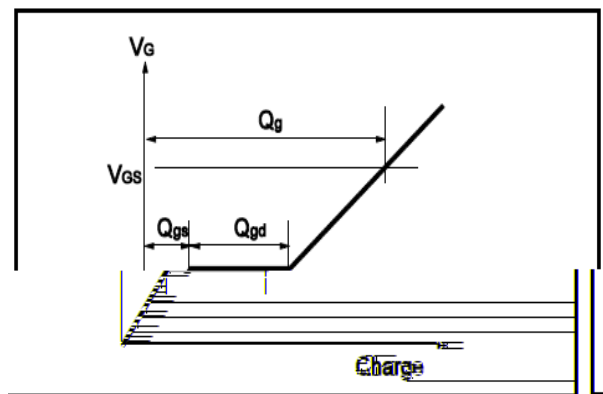


Fig.11 Switching Time Measurement Circuit

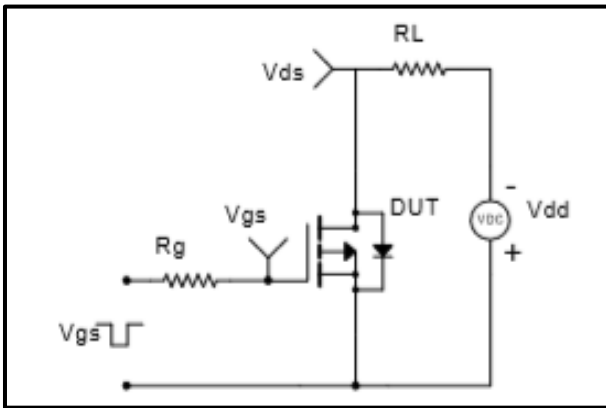
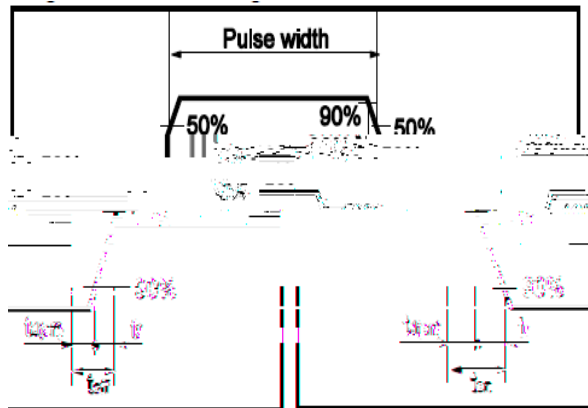
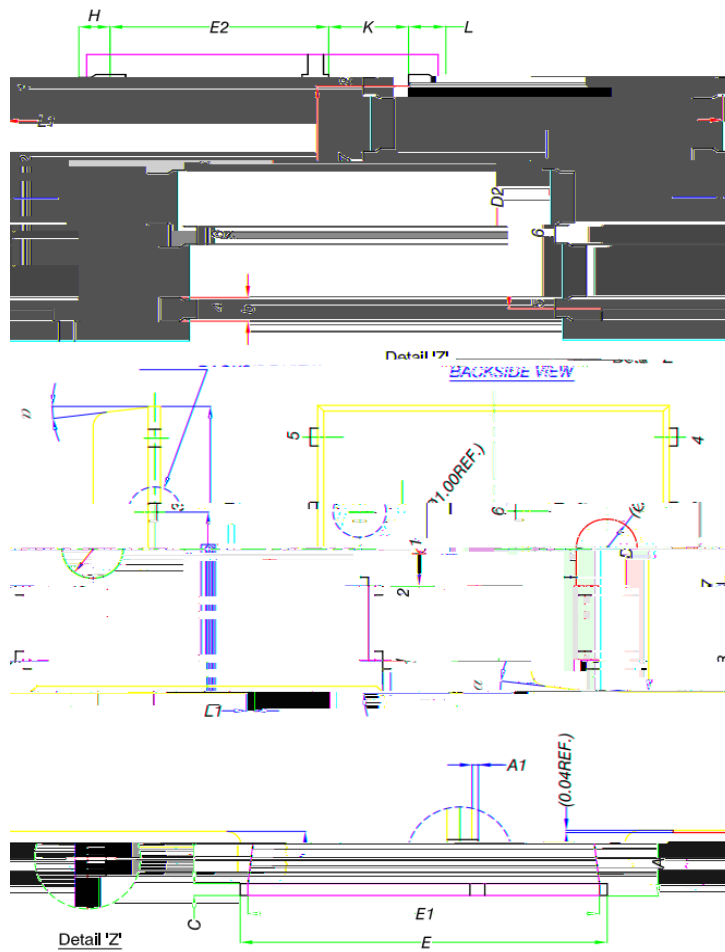


Fig.12 Gate Charge Waveform





Unit mm



MILLIMETERS

	4.80	4.90	5.00
$\phi 2$	3.67	3.81	3.96
	5.90	6.00	6.10
E1	5.20	5.28	5.30
$\phi 2$	4.78	4.88	4.90
$\phi 1$	1.27	1.27 BSC	
	0.41	0.51	0.61
	1.10	K	
		0.51	0.61
		0.51	0.06
		12°	